

Experimental report

20/03/2019

Proposal: 5-23-707

Council: 4/2018

Title: Structure Property Relationships of the Insulator-Insulator Transition in CeMnAsO_{1-x}F_x (x = 0.00 - 0.08)

Research area: Chemistry

This proposal is a new proposal

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Samples: CeMnAsO

CeMnAsO0.965F0.035
CeMnAsO0.94F0.06
CeMnAsO0.925F0.075
CeMnAsO0.92F0.08
CeMnAsO0.97F0.03
CeMnAsO0.95F0.05

Instrument	Requested days	Allocated days	From	To
D20	2	2	19/09/2018	21/09/2018
D2B	2	3	18/10/2018	21/10/2018

Abstract:

CeMnAsO is a Mott insulator and an unusual insulator-insulator transition is observed at low temperature upon electron doping, by substituting F- for O2-. CeMnAsO_{1-x}F_x (x = 0 - 0.08) have been synthesised. Below the transition temperature, TII, the resistivity is observed to increase by > 3 orders of magnitude over a 5 K temperature range for CeMnAsO_{1-x}F_x (x > 0.03). The preliminary results strongly suggest that the unusual insulator-insulator transition is a result of many body localisation (MBL) of the electrons which has not been previously reported in a bulk electronic phase. The proposed MBL phase is only observed over a narrow doping range (x = 0.035 - 0.075 inclusive). We propose to investigate the electronic phase diagram of CeMnAsO_{1-x}F_x by determining if there is any correlation between TII and bond lengths/angles. We also want to verify the stoichiometry of the different phases and determine how the Mn spin transition changes with electron doping.

Experiment 5-23-707

Structure Property Relationships of the Insulator-Insulator Transition in CeMnAsO_{1-x}F_x (x = 0.00 - 0.075)

CeMnAsO is a Mott insulator and an unusual insulator-insulator transition is observed at low temperature upon electron doping. Below TII the resistivity is observed to increase by > 3 orders of magnitude over a 5 K temperature range for CeMnAsO_{1-x}F_x (x > 0.03). Many body localisation (MBL) is an emergent quantum feature and is currently a subject of much debate. It is thought to arise in interacting systems where quantum mechanics overcomes the thermalisation of statistical mechanics. A notable characteristic of MBL systems is that below a transition temperature (T_{II}) they will become perfect insulators, exhibiting zero thermal and electrical conductivity. The CeMnAsO_{1-x}F_x phases investigated so far display all of the characteristics proposed for the MBL phase such as time dependence of the MBL transition temperature and strong sensitivity of the resistivity to the applied current.

In this experiment we have investigated structure property relationships across the series CeMnAsO_{1-x}F_x (x = 0.00 - 0.075). The data were recorded at 290 K on the high resolution diffractometer D2B for four hours for each sample. Preliminary results are given below:

Increasing the F⁻ content up to 5% decreases the unit cell parameters, with the largest magnitude difference observed in the c parameter (**Figure 1**). In general, this can be attributed to a combination of factors, namely the thickness of the component CeO/F and MnAs tetrahedral layers in addition to the distance between these layers (interlayer spacing).

The data obtained from the neutron refinements are given in **Table 1**. The variation of the cell parameters and selected bond angles are given in **Figures 1-2**.

Table 1: Neutron refinement results for CeMnAsO_{1-x}F_x at 300 K, including cell parameters, atomic parameters, agreement factors, and selected bond lengths and angles.

Atom		CeMnAsO _{1-x} F _x			
	x =	0.0	3.5	5.0	7.5
Ce	z	0.1319(2)	0.1321(2)	0.1326(3)	0.1330(3)
	U_{iso} / Å ²	0.0052(5)	0.0047(5)	0.0037(9)	0.0038(8)
Mn	U_{iso} / Å ²	0.0057(5)	0.0070(5)	0.0068(8)	0.0063(7)
	Occupancy	0.972(6)	0.987(6)	0.976(8)	0.984(7)
O/F	z	0.6714(2)	0.6713(2)	0.6718(3)	0.6713(2)
	U_{iso} / Å ²	0.0056(5)	0.0058(5)	0.0050(8)	0.0061(7)
	U_{iso} / Å ²	0.0057(4)	0.0052(4)	0.0046(7)	0.0051(6)
	a / Å	4.09197(2)	4.09071(5)	4.09017(8)	4.09107(7)
	c / Å	8.9718(2)	8.9675(2)	8.9646(2)	8.9678(2)
	χ^2 / %	1.31	1.72	1.13	1.36
	R _P / %	3.37	3.41	3.30	3.66

R _{WP} / %	4.27	4.48	4.15	4.75
V / Å ³	150.226(4)	150.061(5)	149.973(8)	150.093(7)
Ce—O/F / Å	2.3635(10)	2.3636(9)	2.3655(14)	2.3676(12)
Mn—As / Å	2.5593(10)	2.5579(9)	2.5603(15)	2.5581(12)
Ce—O/F—Ce (1) / °	119.91(8)	119.85(7)	119.66(12)	119.53(10)
Ce—O/F—Ce (2) / °	104.52(4)	104.55(3)	104.63(5)	104.69(4)
Mn—As—Mn (1) / °	111.16(3)	111.14(3)	111.22(4)	111.14(4)
Mn—As—Mn (2) / °	106.15(6)	106.19(6)	106.03(9)	106.19(7)
Ce—As / Å	3.3893(10)	3.3876(9)	3.3821(14)	3.3838(12)
Mn—Mn / Å	2.89346(2)	2.89257(8)	2.89219(11)	2.89282(10)
MnAs layer / Å	3.07498(191)	3.07197(179)	3.08062(277)	3.07226(232)
CeO/F layer / Å	2.36669(251)	2.36897(230)	2.37758(358)	2.38453(296)
Interlayer spacing / Å	1.76507(192)	1.76327(178)	1.75318(277)	1.75550(231)
Mn moment / μ _B	2.55(2)	2.52(2)	2.56(3)	2.49(3)

Previous studies on the structurally related iron arsenide superconductors highlighted that an increasing T_c was correlated to increasingly regular FeAs₄ tetrahedra [1–5]. As the F content increases in the Mn samples, the Ce—O/F—Ce bond angles progressively become closer to those of an ideal tetrahedron; the As—Mn—As bond angles do not show a regular trend, but this is presumably due to the As non-stoichiometry in each sample (Table 1, Figure 2).

Figures

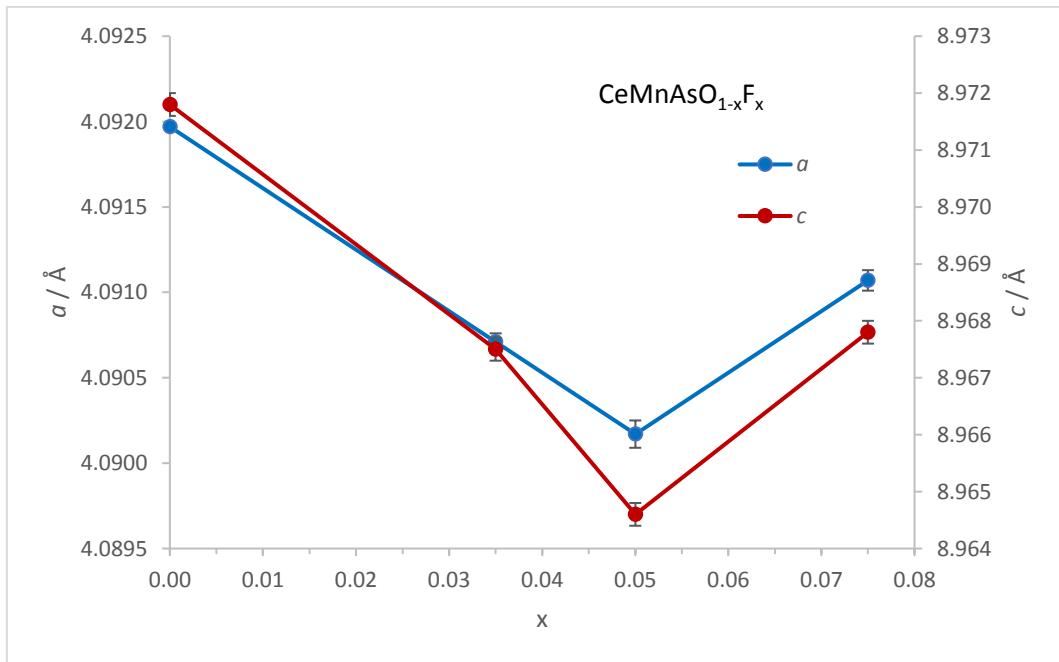


Figure 1: Variation of cell parameters for CeMnAsO_{1-x}F_x (x = 0.0, 3.5, 5.0, and 7.5)

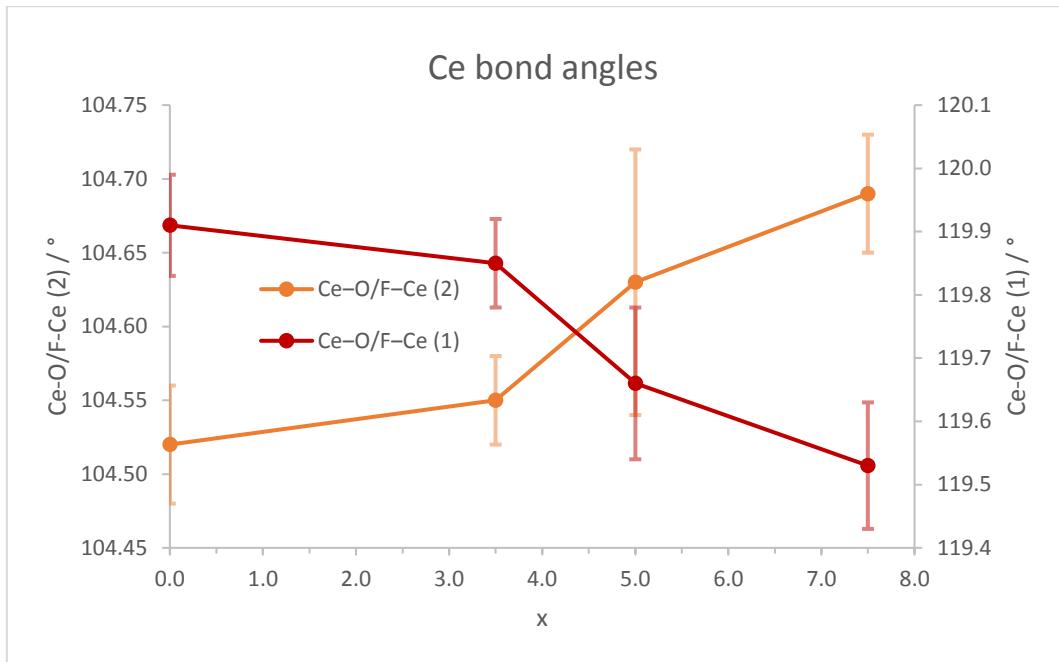


Figure 2: Variation in Ce–O/F–Ce bond angles

References

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